ITI CMOS Analog IC Design 2024 Lab 06 Differential Amplifier

Part 1: Differential Amplifier Design

1. We want to design a resistive loaded differential amplifier with the specifications below.

Parameter	
Supply (V_{DD})	1.8 V
Bias Current (Iss)	40 μΑ
Deferential gain	8
CM output level	$V_{DD}/3$
Load capacitance	1 pf

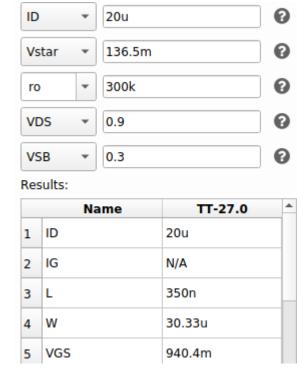
- 2. Since the required output level is closer to the ground rail, we will use a PMOS input stage
- 3. Choose *RD* to meet the CM output level spec. As we want CM output level = .6 V so $Iss/2*RD=.6 \text{ so } RD=30 \text{ k}\Omega$
- 4. The differential amplifier gain is given by $|Av| \approx gm(RD||ro)$
- 5. We will choose L to set $ro \gg RD \rightarrow ro = 10 * RD$

$$|Av| \approx 0.91 \times gm * RD = 0.91 \times \frac{2ID}{V*} \times RD = \frac{1.82VRD}{V*}$$

6. **Choose** V * to meet the differential gain spec.

$$V * = \frac{1.82VRD}{|Av|}$$
 as $VRD = .6V$ and $|Av| = 8$ so $V * = 1.82 * \frac{.6}{8} = 136.5 mV$

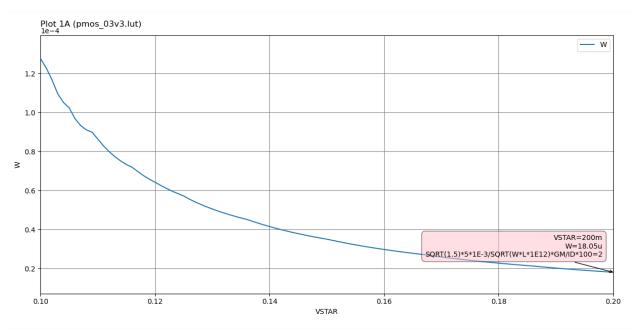
- 7. Assume we will set *VDS* of the tail current source to 300mV to allow more output swing. Report the input pair sizing
- So, we need L=350 nm and W=30.33 μm to meet the above specs for input pair
- 8. Given the above assumption for *VDS* of the tail current source, **calculate** the required CM input level
- As we set *VDS* of the tail current source = 300mV and Vgs is 940 mV so the CM input level = 1800-300-940 = 560 mV
- 9. The tail current source has the following specifications:

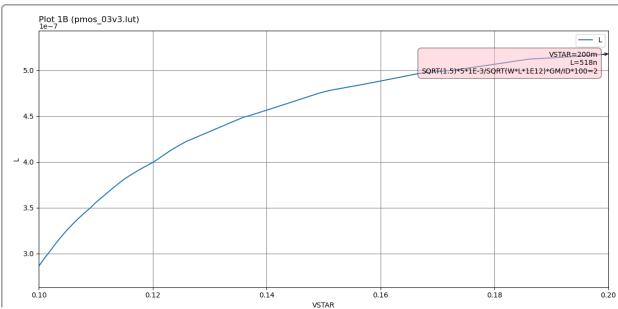


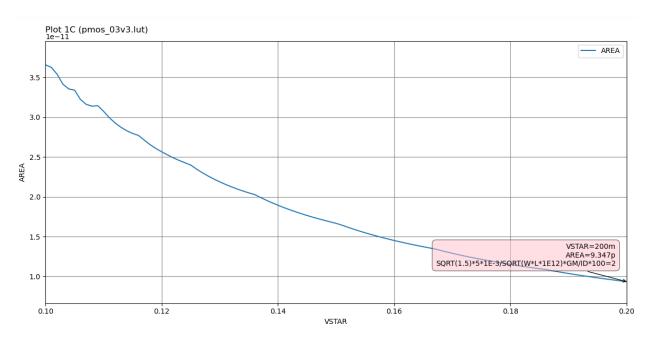
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Parameter	
Input current	$20\mu A$
Percent mismatch: $\sigma(I_{out})/I_{out}$	≤ 2%
Compliance voltage	≤ 200mV
Area	Minimize

10.Use SA to plot the sizing at a constant $\sigma(lout)/lout$.



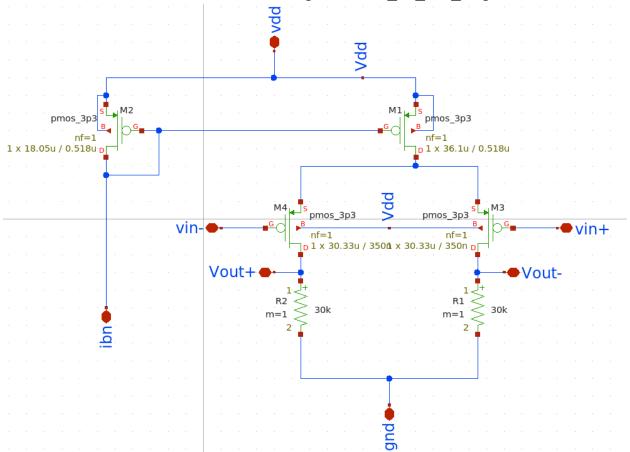




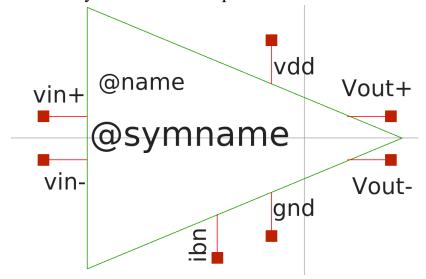
- 11. As seen in the plot above, for a given mismatch requirement, the minimum area is achieved at the max V*
- 12. The plot also shows that at a given V* (compliance voltage), going for lower mismatch necessitates longer L
- 13. Given the compliance voltage spec
- As we choose $V^*=200 \text{ mV}$ so we need L=518 nm &W=18.05 μm
- 14. **Calculate** the min and max CM input levels. Is the previously selected CM input level in the valid range?
- the minimum =- Vth+VRD
- Vth ≈ 870 mV so minimum = -870+600=-270 mV
- The max CM input level = 1800-200-940 = 660 my
- So, 560 mV as an input is in the valid range

Part 2: Differential Amplifier Simulation

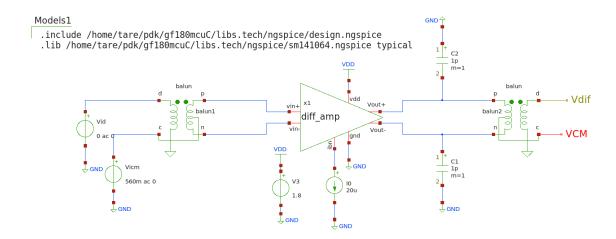
1. Create the schematic of a differential amplifier "lab_06_diff_amp".



2. Create a symbol for the diff pair



3. Create a new cell for the testbench



1. OP (Operating Point) Analysis

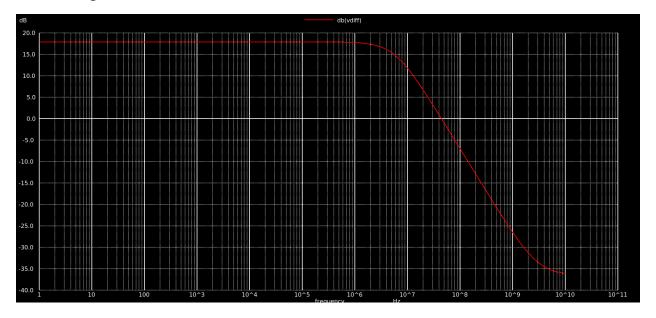
```
BSIM4v5: Berkeley Short Channel IGFET Model-4
    device
                       m.x1.xm2.m0
                                                                       m.x1.xm3.m0
                                               m.x1.xm1.m0
                      pmos_3p3.13
                                               pmos_3p3.13
                                                                       pmos_3p3.12
     model
        id
                             2e-05
                                               3.99621e-05
                                                                       2.01658e-05
                          0.943347
                                                  0.943347
                                                                          0.940154
       vgs
       vds
                          0.943346
                                                  0.299842
                                                                          0.895181
                          0.792643
                                                                          0.871942
       vth
                                                  0.788519
                          0.166242
                                                                          0.120203
     vdsat
                                                    0.1693
                       0.000205196
                                               0.000400795
                                                                       0.000292557
        \mathsf{gm}
       gds
                       1.01221e-06
                                               6.26859e-06
                                                                        3.2354e-06
      gmbs
                       9.18684e-05
                                               0.000179579
                                                                       9.52331e-05
BSIM4v5: Berkeley Short Channel IGFET Model-4
    device
                      m.x1.xm4.m0
     model
                      pmos_3p3.12
        id
                       1.97963e-05
       vgs
                          0.940154
       vds
                          0.906264
       vth
                          0.873229
                          0.119342
     vdsat
                      0.000288765
       gds
                      3.17534e-06
                       9.39851e-05
      gmbs
```

- As Vds > 1.2*Vdsat for all transistor so all transistors are in saturation region

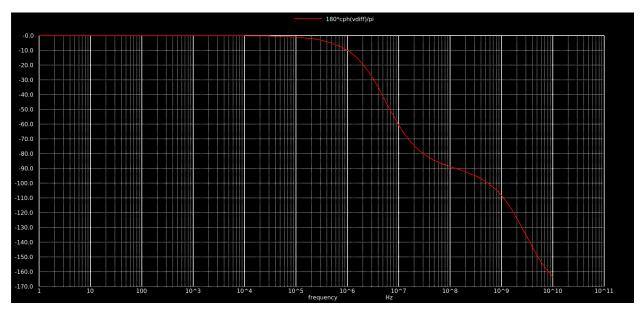
2. Diff small signal ccs:

- Use AC magnitude = 1 for the diff source (and AC magnitude = 0 for the CM source)
- Run AC analysis (1Hz:10GHz, logarithmic, 10 points/decade).

- Report the Bode plot of small signal diff gain.
- Magnitude



- phase



- Bandwidth and gain from simulation

```
gain = 7.856643e+00 at= 1.000000e+00
bw = 5.686016e+06
```

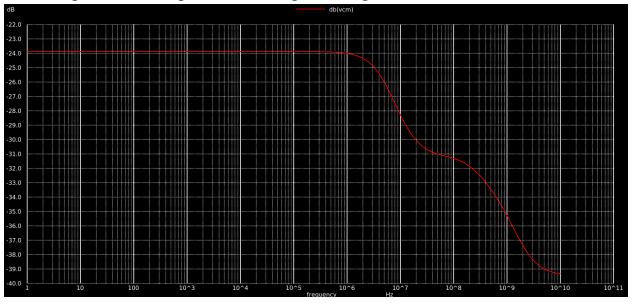
- hand analysis for gain: as gm4 \approx gm3 \approx 290 μ S and gds4 \approx gds3 \approx 3.2 μ S so gain =gm*(RD||1/gds)=7.94

-	for bandwidth: ω	=	$\frac{1}{2\pi*(RD ro)CL}$	=	5.81	MHz
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	Analytical	Simulation
Gain	7.94	7.86
Bandwidth(MHz)	5.81	5.69

3. CM small signal ccs:

- Use AC magnitude = 1 for the CM source (and AC magnitude = 0 for the diff source).
- Run AC analysis (1Hz:10GHz, logarithmic, 10 points/decade).
- Report the Bode plot of small signal CM gain.



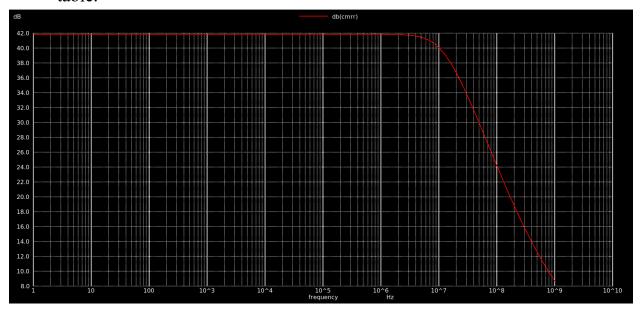
- Compare the DC CM gain with hand analysis in a table.
- As gm4 \approx gm3 \approx 290 μ S and gmbs4 \approx gmbs3 \approx 95 μ S CM gain

$$Avcm = \frac{gm * RD}{(1 + (gm + gmb) * 2Rss)} = .070$$

	Analytical	Simulation
Avcm	.07	.64

- The gain is less than 1 as the differential amplifier attenuate the CM signal and complete cancel it when we subtract Vout+ Vout-
- As there are pole around 5.6MHz the magnitude decreases after it but there are zero from the tail current source as it has a resistance and there is a bypass capacitance in this node, and this make the magnitude flat and decrease again as there are other poles in the circuit in the same node

- Plot Avd/Avcm in dB. Compare Avd/Avcm @ DC with hand analysis in a table.



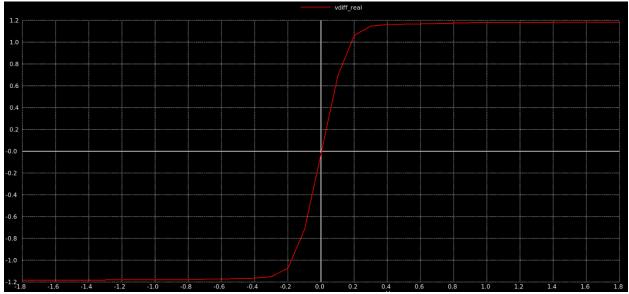
-
$$CMRR = (gm + gms) * 2Rss = (290 + 90) * 10^{-6} * \frac{2}{6.269 * 10^{-6}} = 121.23$$

	Analytical	Simulation
CMRR	121.23	122.3

- As the Avd and Avcm decrease with the same ratio after the pole around 5.6MHz the CMRR don't decrease at this pole but at the zero in the tail current source and attach Rss to the ground and make Avcm don't decrease as Avd anymore it's decrease with low rate than Avd so CMRR decrease as Avd don't increase at this zero as differential amplifier acts as a virtual ground at this node and don't see Rss and the cacitance in this node

4. Diff large signal ccs:

- Use dc sweep (not parametric sweep) for Vid = -VDD:10m:VDD



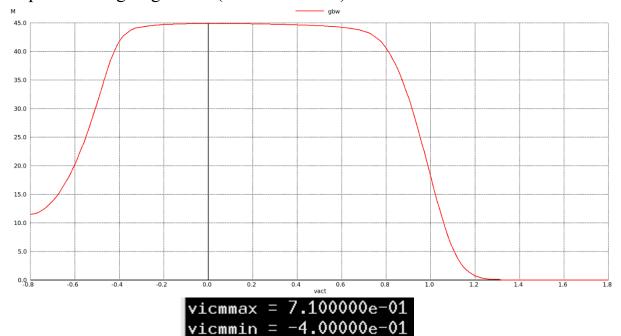
```
No. of Data Rows : <u>37</u>
vdifflow
                         -1.182298e+00 at= -1.800000e+00
vdiffzer0
                         -1.651474e-02
vdiffhigh
                      = 1.182144e+00 at= 1.700000e+00
BSIM4v5: Berkeley Short Channel IGFET Model-4
     device
                        m.x1.xm2.m0
                                                                           m.x1.xm3.m0
                                                  m.x1.xm1.m0
                        pmos_3p3.13
                                                 pmos_3p3.13
3.94097e-05
      {\sf model}
                                                                           pmos_3p3.12
                                                                           1.11617e-20
          id
BSIM4v5: Berkeley Short Channel IGFET Model-4
                        m.\times1.\times m4.m0
     device
                        pmos_3p3.12
3.941e-05
      model
```

- As we see the current at Vid=VDD = 39.41 μ A so Vdiff@Vid=VDD = 39.41 μ A *30k Ω - 0 =1.18V and at Vid=-VDD the current will be the same but in the other branch so Vdiff@Vid=-VDD = 0-39.41 μ A *30k Ω = -1.18V at Vid=0 the same current will through in each branch so the Vdiff = 0

	Analytical	Simulation
Vdiff@Vid=-VDD	-1.18	-1.182
Vdiff@Vid=0	0	-0.0165
Vdiff@Vid=VDD	1.18	1.1182

5. CM large signal ccs (GBW vs Vicm):

- We will use parametric sweep on AC analysis to get GBW.
- Report CM large signal ccs (GBW vs VICM)



- the minimum =- Vth+VRD
- Vth ≈ 870 mV so minimum = -870+600=-270 mV
- The max CM input level = VDD-Vdsat1-Vgs3,4= 1800-169-940 = 691 mv

	Analytical	Simulation
VICM max (mV)	691	710
VICM min (mV)	-270	-400